

# MCP660/1/2/3/4/5/9

# 60 MHz, 6 mA Op Amps

## Features

- Gain Bandwidth Product: 60 MHz (typical)
- Short Circuit Current: 90 mA (typical)
- Noise: 6.8 nV/√Hz (typical, at 1 MHz)
- Rail-to-Rail Output
- Slew Rate: 32 V/µs (typical)
- Supply Current: 6.0 mA (typical)
- Power Supply: 2.5V to 5.5V
- Extended Temperature Range: -40°C to +125°C

# **Typical Applications**

- Driving A/D Converters
- Power Amplifier Control Loops
- Barcode Scanners
- Optical Detector Amplifier

# **Design Aids**

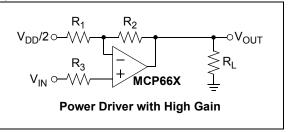
- SPICE Macro Models
- FilterLab<sup>®</sup> Software
- Microchip Advanced Part Selector (MAPS)
- Analog Demonstration and Evaluation Boards
- Application Notes

# Description

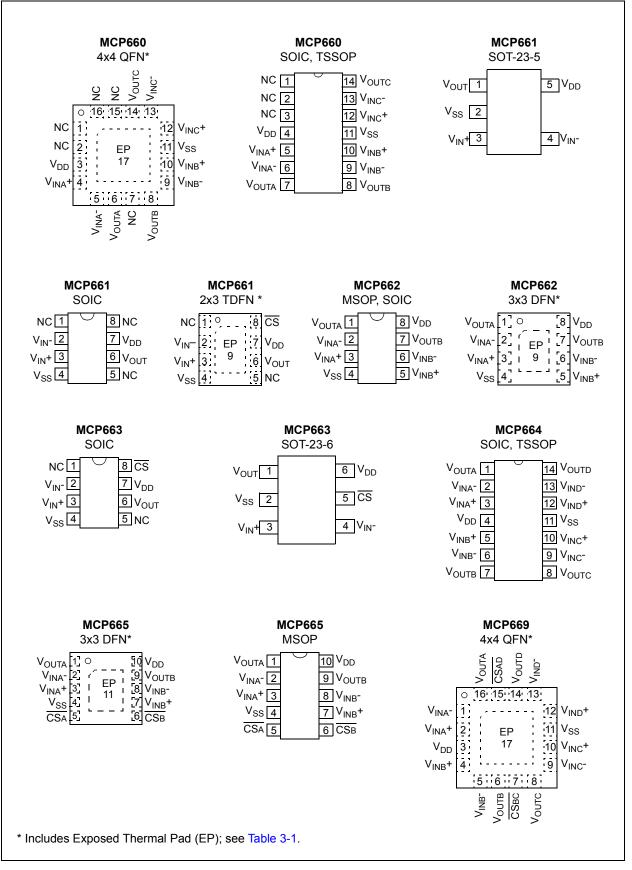
The Microchip Technology, Inc. MCP660/1/2/3/4/5/9 family of operational amplifiers (op amps) features high gain bandwidth product (60 MHz, typical) and high output short circuit current (90 mA, typical). Some also provide a Chip Select pin  $\overline{(CS)}$  that supports a Low Power mode of operation. These amplifiers are optimized for high speed, low noise and distortion, single-supply operation with rail-to-rail output and an input that includes the negative rail.

This family is offered in single (MCP661), single with  $\overline{CS}$  pin (MCP663), dual (MCP662) and dual with two  $\overline{CS}$  pins (MCP665), triple (MCP660), quad (MCP664) and quad with two  $\overline{CS}$  pins (MCP669). All devices are fully specified from -40°C to +125°C.

# **Typical Application Circuit**



# Package Types



# 1.0 ELECTRICAL CHARACTERISTICS

# 1.1 Absolute Maximum Ratings †

V <sub>DD</sub> – V <sub>SS</sub> 6.5V
Current at Input Pins±2 mA
Analog Inputs (V <sub>IN</sub> + and V <sub>IN</sub> -) $\uparrow \uparrow$ . V <sub>SS</sub> – 1.0V to V <sub>DD</sub> + 1.0V
All other Inputs and Outputs $V_{SS}$ – 0.3V to $V_{DD}$ + 0.3V
Output Short Circuit Current Continuous
Current at Output and Supply Pins±150 mA
Storage Temperature65°C to +150°C
Max. Junction Temperature+150°C
ESD protection on all pins (HBM, MM)≥ 1 kV, 200V

**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

**††** See Section 4.1.2 "Input Voltage and Current Limits".

# 1.2 Specifications

# TABLE 1-1: DC ELECTRICAL SPECIFICATIONS

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25$  °C,  $V_{DD} = +2.5V$  to +5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 1 \text{ k}\Omega$  to  $V_L$  and  $\overline{CS} = V_{SS}$  (refer to Figure 1-2).

Parameters	Sym	Min	Тур	Max	Units	Conditions
Input Offset						
Input Offset Voltage	V <sub>OS</sub>	-8	±1.8	+8	mV	
Input Offset Voltage Drift	$\Delta V_{OS} / \Delta T_A$	—	±2.0	—	µV/°C	T <sub>A</sub> = -40°C to +125°C
Power Supply Rejection Ratio	PSRR	61	76	_	dB	
Input Current and Impedance						
Input Bias Current	I <sub>B</sub>	—	6	—	pА	
Across Temperature	I <sub>B</sub>	—	130	—	pА	T <sub>A</sub> = +85°C
Across Temperature	I <sub>B</sub>	—	1700	5,000	pА	T <sub>A</sub> = +125°C
Input Offset Current	I <sub>OS</sub>	—	±10	_	pА	
Common Mode Input Impedance	Z <sub>CM</sub>	—	10 <sup>13</sup>   9	—	Ω  pF	
Differential Input Impedance	Z <sub>DIFF</sub>	—	10 <sup>13</sup>   2	—	Ω  pF	
Common Mode						
Common-Mode Input Voltage Range	V <sub>CMR</sub>	$V_{SS} - 0.3$		V <sub>DD</sub> – 1.3	V	(Note 1)
Common-Mode Rejection Ratio	CMRR	64	79	_	dB	$V_{DD}$ = 2.5V, $V_{CM}$ = -0.3 to 1.2V
	CMRR	66	81	—	dB	$V_{DD}$ = 5.5V, $V_{CM}$ = -0.3 to 4.2V
Open Loop Gain						
DC Open Loop Gain (large signal)	A <sub>OL</sub>	88	117	—	dB	V <sub>DD</sub> = 2.5V, V <sub>OUT</sub> = 0.3V to 2.2V
	A <sub>OL</sub>	94	126	—	dB	V <sub>DD</sub> = 5.5V, V <sub>OUT</sub> = 0.3V to 5.2V

**Note 1:** See Figure 2-5 for temperature effects.

2: The I<sub>SC</sub> specifications are for design guidance only; they are not tested.

# TABLE 1-1: DC ELECTRICAL SPECIFICATIONS (CONTINUED)

**Electrical Characteristics:** Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = +2.5V$  to +5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} \approx V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 1 \text{ k}\Omega$  to  $V_L$  and  $\overline{CS} = V_{SS}$  (refer to Figure 1-2).

Sym	Min	Тур	Max	Units	Conditions					
Output										
V <sub>OL</sub> , V <sub>OH</sub>	V <sub>SS</sub> + 25	_	V <sub>DD</sub> - 25	mV	V <sub>DD</sub> = 2.5V, G = +2, 0.5V Input Overdrive					
V <sub>OL</sub> , V <sub>OH</sub>	V <sub>SS</sub> + 50	_	$V_{DD}-50$	mV	V <sub>DD</sub> = 5.5V, G = +2, 0.5V Input Overdrive					
I <sub>SC</sub>	±45	±90	±145	mA	V <sub>DD</sub> = 2.5V (Note 2)					
I <sub>SC</sub>	±40	±80	±150	mA	V <sub>DD</sub> = 5.5V (Note 2)					
Power Supply										
V <sub>DD</sub>	2.5	_	5.5	V						
Ι <sub>Q</sub>	3	6	9	mA	No Load Current					
	$V_{OL}, V_{OH}$ $V_{OL}, V_{OH}$ $I_{SC}$ $I_{SC}$	$\begin{array}{c c} V_{OL}, V_{OH} & V_{SS} + 25 \\ \hline V_{OL}, V_{OH} & V_{SS} + 50 \\ \hline I_{SC} & \pm 45 \\ \hline I_{SC} & \pm 40 \\ \hline \end{array}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $					

**Note 1:** See Figure 2-5 for temperature effects.

**2:** The I<sub>SC</sub> specifications are for design guidance only; they are not tested.

# TABLE 1-2: AC ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless indicated, T <sub>A</sub> = +25°C, V <sub>DD</sub> = +2.5V to +5.5V, V <sub>SS</sub> = GND, V <sub>CM</sub> = V <sub>DD</sub> /2,
$V_{OUT} \approx V_{DD}/2$ , $V_L = V_{DD}/2$ , $R_L = 1 \text{ k}\Omega$ to $V_L$ , $C_L = 20 \text{ pF}$ and $\overline{CS} = V_{SS}$ (refer to Figure 1-2).

Parameters	Sym	Sym Min Typ Max Uni		Units	s Conditions		
AC Response							
Gain Bandwidth Product	GBWP		60		MHz		
Phase Margin	PM	_	65	_	0	G = +1	
Open Loop Output Impedance	R <sub>OUT</sub>	—	10	—	Ω		
AC Distortion							
Total Harmonic Distortion plus Noise	THD+N		0.003	_	%	G = +1, V <sub>OUT</sub> = 2V <sub>P-P</sub> , f = 1 kHz, V <sub>DD</sub> = 5.5V, BW = 80 kHz	
Differential Gain, Positive Video (Note 1)	DG	_	0.3	—	%	NTSC, $V_{DD}$ = +2.5V, $V_{SS}$ = -2.5V, G = +2, $V_L$ = 0V, DC $V_{IN}$ = 0V to 0.7V	
Differential Gain, Negative Video (Note 1)	DG		0.3	_	%	NTSC, $V_{DD}$ = +2.5V, $V_{SS}$ = -2.5V, G = +2, $V_L$ = 0V, DC $V_{IN}$ = 0V to -0.7V	
Differential Phase, Positive Video (Note 1)	DP	_	0.3	—	0	NTSC, $V_{DD}$ = +2.5V, $V_{SS}$ = -2.5V, G = +2, $V_L$ = 0V, DC $V_{IN}$ = 0V to 0.7V	
Differential Phase, Negative Video (Note 1)	DP	—	0.9	—	o	NTSC, $V_{DD}$ = +2.5V, $V_{SS}$ = -2.5V, G = +2, $V_L$ = 0V, DC $V_{IN}$ = 0V to -0.7V	
Step Response			1		1		
Rise Time, 10% to 90%	t <sub>r</sub>		5	_	ns	G = +1, V <sub>OUT</sub> = 100 mV <sub>P-P</sub>	
Slew Rate	SR		32		V/µs	G = +1	
Noise							
Input Noise Voltage	E <sub>ni</sub>	—	14	—	μV <sub>P-P</sub>	f = 0.1 Hz to 10 Hz	
Input Noise Voltage Density	e <sub>ni</sub>	—	6.8	—	nV/√Hz	f = 1 MHz	
Input Noise Current Density	i <sub>ni</sub>		4	_	fA/√Hz	f = 1 kHz	

**Note 1:** These specifications are described in detail in **Section 4.3 "Distortion**". (NTSC refers to a National Television Standards Committee signal.)

Electrical Characteristics: Unles								
$V_{OUT} \approx V_{DD}/2$ , $V_L = V_{DD}/2$ , $R_L = 1 \text{ k}\Omega$ to $V_L$ , $C_L = 20 \text{ pF}$ and $\overline{CS} = V_{SS}$ (refer to Figure 1-1 and Figure 1-2).								
Parameters	Sym	Min	Тур	Max	Units	Conditions		
CS Low Specifications								
CS Logic Threshold, Low	V <sub>IL</sub>	$V_{SS}$	—	0.2V <sub>D</sub>	V			
CS Input Current, Low	I <sub>CSL</sub>	_	-0.1	_	nA	$\overline{CS} = 0V$		
CS High Specifications								
CS Logic Threshold, High	V <sub>IH</sub>	0.8V <sub>D</sub> D		$V_{DD}$	V			
CS Input Current, High	I <sub>CSH</sub>		-0.7	_	μA	$\overline{\text{CS}} = \text{V}_{\text{DD}}$		
GND Current	I <sub>SS</sub>	-2	-1	_	μA			
CS Internal Pull Down Resistor	R <sub>PD</sub>		5	_	MΩ			
Amplifier Output Leakage	I <sub>O(LEAK</sub> )		40	—	nA	$\overline{\text{CS}}$ = V <sub>DD</sub> , T <sub>A</sub> = +125°C		
CS Dynamic Specifications								
CS Input Hysteresis	V <sub>HYST</sub>	—	0.25	—	V			
CS High to Amplifier Off Time (output goes High-Z)	t <sub>OFF</sub>		200		ns	$\frac{G = +1 \text{ V/V}, \text{ V}_{\text{L}} = \text{V}_{\text{SS}}}{CS} = 0.8\text{V}_{\text{DD}} \text{ to } \text{V}_{\text{OUT}} = 0.1(\text{V}_{\text{DD}}/2)$		
CS Low to Amplifier On Time	t <sub>ON</sub>		2	10	μs	$\frac{G}{CS} = +1 V/V, V_{L} = V_{SS}, \\ \frac{G}{CS} = 0.2V_{DD} \text{ to } V_{OUT} = 0.9(V_{DD}/2)$		

# TABLE 1-3: DIGITAL ELECTRICAL SPECIFICATIONS

#### TABLE 1-4: TEMPERATURE SPECIFICATIONS

Electrical Characteristics: Unless in	Electrical Characteristics: Unless indicated, all limits are specified for: V <sub>DD</sub> = +2.5V to +5.5V, V <sub>SS</sub> = GND.								
Parameters	Sym	Min	Тур	Max	Units	Conditions			
Temperature Ranges									
Specified Temperature Range	T <sub>A</sub>	-40	—	+125	°C				
Operating Temperature Range	T <sub>A</sub>	-40	_	+125	°C	(Note 1)			
Storage Temperature Range	T <sub>A</sub>	-65	_	+150	°C				
Thermal Package Resistances			•						
Thermal Resistance, 5L-SOT-23	$\theta_{JA}$		220.7		°C/W				
Thermal Resistance, 6L-SOT-23	θ <sub>JA</sub>		190.5	_	°C/W				
Thermal Resistance, 8L-3x3 DFN	$\theta_{JA}$	—	56.7	_	°C/W	(Note 2)			
Thermal Resistance, 8L-MSOP	$\theta_{JA}$		211	_	°C/W				
Thermal Resistance, 8L-SOIC	$\theta_{JA}$		149.5	_	°C/W				
Thermal Resistance, 8L-2x3 TDFN	θ <sub>JA</sub>		52.5	_	°C/W				
Thermal Resistance, 10L-3x3 DFN	$\theta_{JA}$		53.3	_	°C/W	(Note 2)			
Thermal Resistance, 10L-MSOP	$\theta_{JA}$		202	_	°C/W				
Thermal Resistance, 14L-SOIC	$\theta_{JA}$		95.3	_	°C/W				
Thermal Resistance, 14L-TSSOP	$\theta_{JA}$	—	100		°C/W				
Thermal Resistance, 16L-QFN	θ <sub>JA</sub>	—	45.7		°C/W				

**Note 1:** Operation must not cause  $T_J$  to exceed Maximum Junction Temperature specification (+150°C).

**2:** Measured on a standard JC51-7, four layer printed circuit board with ground plane and vias.

# 1.3 Timing Diagram

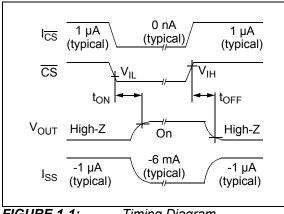


FIGURE 1-1: Timing Diagram.

# 1.4 Test Circuits

The circuit used for most DC and AC tests is shown in Figure 1-2. This circuit can independently set V<sub>CM</sub> and V<sub>OUT</sub>; see Equation 1-1. Note that V<sub>CM</sub> is not the circuit's Common mode voltage ((V<sub>P</sub> + V<sub>M</sub>)/2), and that V<sub>OST</sub> includes V<sub>OS</sub> plus the effects (on the input offset error, V<sub>OST</sub>) of temperature, CMRR, PSRR and A<sub>OL</sub>.

#### **EQUATION 1-1:**

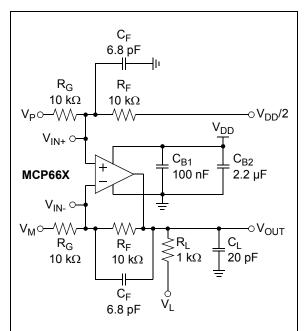
 $G_{DM} = R_F / R_G$   $V_{CM} = (V_P + V_{DD} / 2) / 2$   $V_{OST} = V_{IN-} - V_{IN+}$   $V_{OUT} = (V_{DD} / 2) + (V_P - V_M) + V_{OST} (1 + G_{DM})$ 

Where:

 $G_{DM}$  = Differential Mode Gain (V/V)

 $V_{CM}$  = Op Amp's Common Mode (V) Input Voltage

V<sub>OST</sub> = Op Amp's Total Input Offset (mV) Voltage



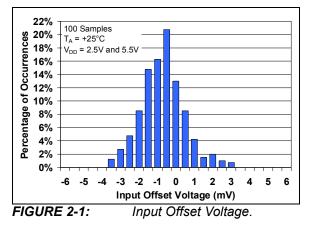
**FIGURE 1-2:** AC and DC Test Circuit for Most Specifications.

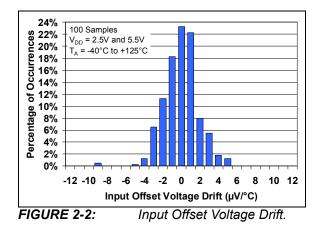
# 2.0 TYPICAL PERFORMANCE CURVES

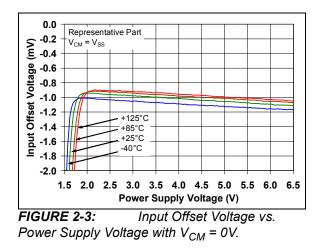
**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

**Note:** Unless indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = +2.5V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 1 \text{ k}\Omega$  to  $V_L$ ,  $C_L = 20 \text{ pF}$  and  $\overline{CS} = V_{SS}$ .

# 2.1 DC Signal Inputs







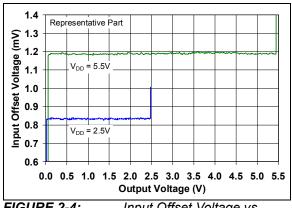
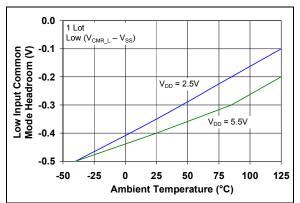
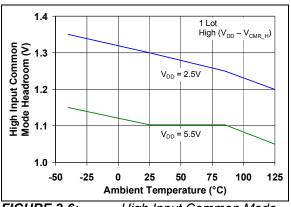
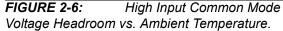


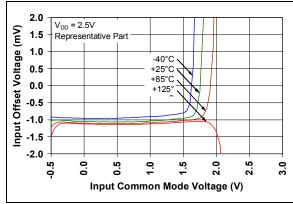
FIGURE 2-4: Input Offset Voltage vs. Output Voltage.



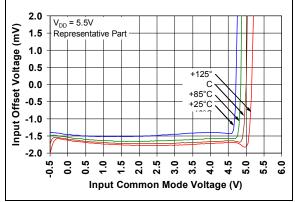
**FIGURE 2-5:** Low Input Common Mode Voltage Headroom vs. Ambient Temperature.



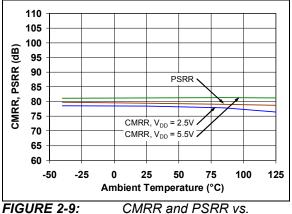




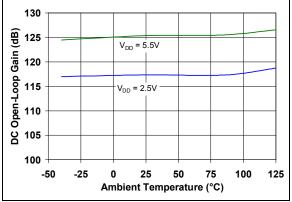
**FIGURE 2-7:** Input Offset Voltage vs. Common Mode Voltage with  $V_{DD} = 2.5V$ .



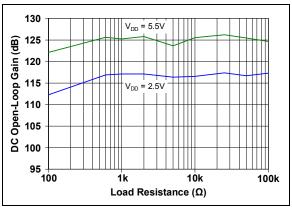
**FIGURE 2-8:** Input Offset Voltage vs. Common Mode Voltage with V<sub>DD</sub> = 5.5V.



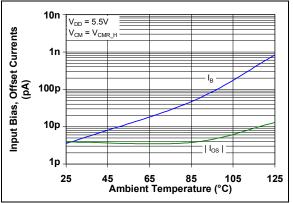
Ambient Temperature.



**FIGURE 2-10:** DC Open-Loop Gain vs. Ambient Temperature.

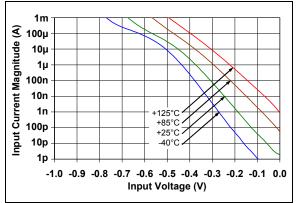


**FIGURE 2-11:** DC Open-Loop Gain vs. Load Resistance.

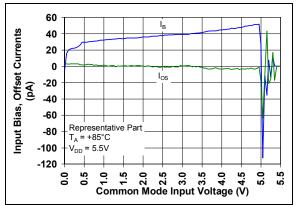


**FIGURE 2-12:** Input Bias and Offset Currents vs. Ambient Temperature with  $V_{DD}$  = +5.5V.

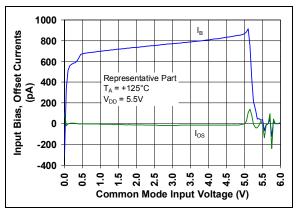
**Note:** Unless indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = +2.5V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 1 \text{ k}\Omega$  to  $V_L$ ,  $C_L = 20 \text{ pF}$  and  $\overline{CS} = V_{SS}$ .



**FIGURE 2-13:** Input Bias Current vs. Input Voltage (below  $V_{SS}$ ).

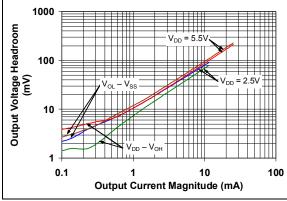


**FIGURE 2-14:** Input Bias and Offset Currents vs. Common Mode Input Voltage with  $T_A = +85^{\circ}C$ .



**FIGURE 2-15:** Input Bias and Offset Currents vs. Common Mode Input Voltage with  $T_A = +125^{\circ}$ C.

# 2.2 Other DC Voltages and Currents



**FIGURE 2-16:** Output Voltage Headroom vs. Output Current.

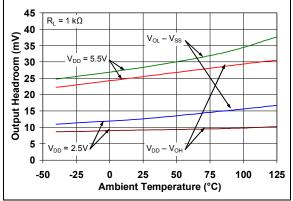


FIGURE 2-17: Output Voltage Headroom vs. Ambient Temperature.

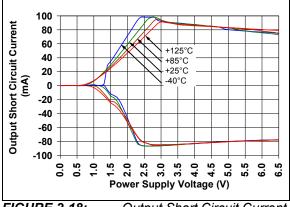


FIGURE 2-18: Output Short Circuit Current vs. Power Supply Voltage.

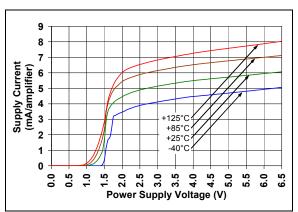


FIGURE 2-19: Supply Current vs. Power Supply Voltage.

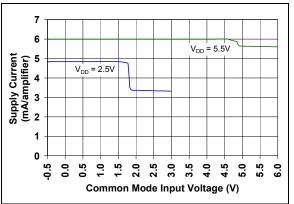


FIGURE 2-20: Supply Current vs. Common Mode Input Voltage.

### 2.3 Frequency Response

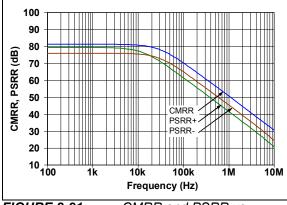
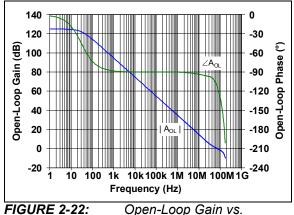
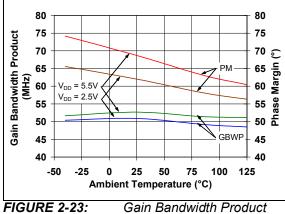


FIGURE 2-21: Frequency.

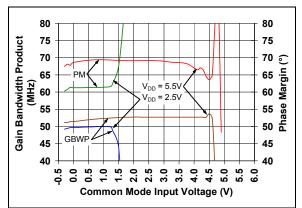
CMRR and PSRR vs.



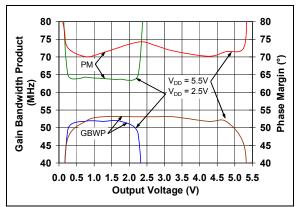
Frequency.



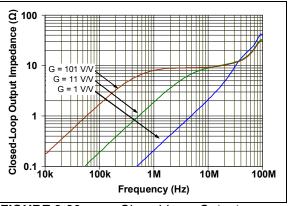
and Phase Margin vs. Ambient Temperature.



**FIGURE 2-24:** Gain Bandwidth Product and Phase Margin vs. Common Mode Input Voltage.



**FIGURE 2-25:** Gain Bandwidth Product and Phase Margin vs. Output Voltage.



**FIGURE 2-26:** Closed-Loop Output Impedance vs. Frequency.

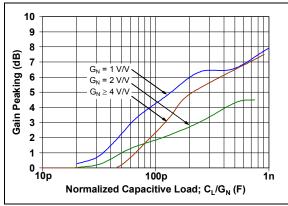


FIGURE 2-27: Gain Peaking vs. Normalized Capacitive Load.

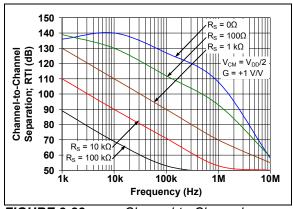


FIGURE 2-28: Channel-to-Channel Separation vs. Frequency.

#### 2.4 Noise and Distortion

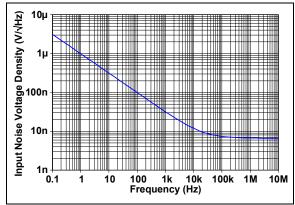
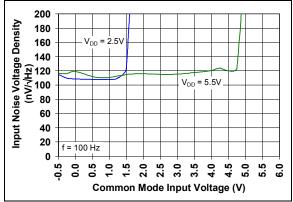
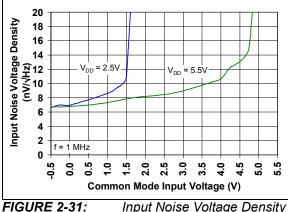


FIGURE 2-29: Input Noise Voltage Density vs. Frequency.



**FIGURE 2-30:** Input Noise Voltage Density vs. Input Common Mode Voltage with f = 100 Hz.



**FIGURE 2-31:** Input Noise Voltage Density vs. Input Common Mode Voltage with f = 1 MHz.

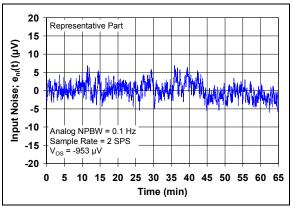


FIGURE 2-32: Input Noise vs. Time with 0.1 Hz Filter.

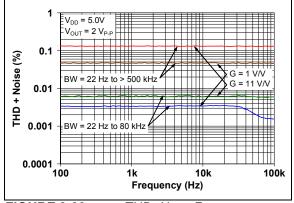
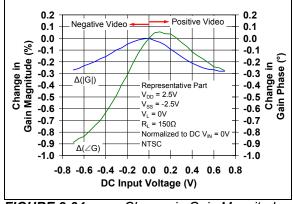


FIGURE 2-33: THD+N vs. Frequency.



**FIGURE 2-34:** Change in Gain Magnitude and Phase vs. DC Input Voltage.

#### 2.5 Time Response

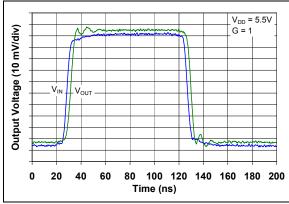
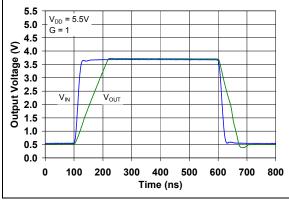


FIGURE 2-35: Non-inverting Small Signal Step Response.



*FIGURE 2-36:* Non-inverting Large Signal Step Response.

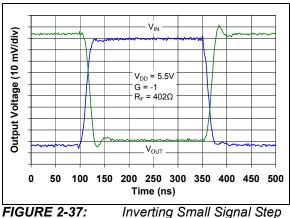


FIGURE 2-37: Inverting Small Signal Step Response.

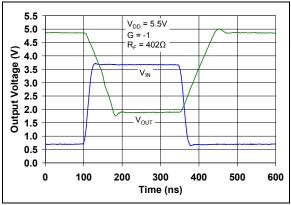
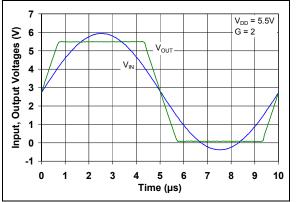
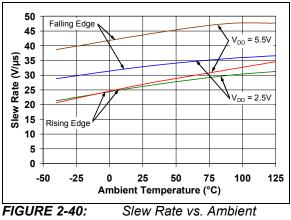


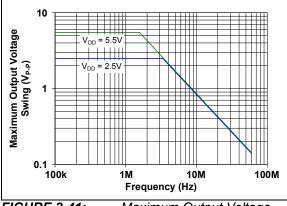
FIGURE 2-38: Inverting Large Signal Step Response.



**FIGURE 2-39:** The MCP660/1/2/3/4/5/9 family shows no input phase reversal with overdrive.



Temperature.



*FIGURE 2-41:* Maximum Output Voltage Swing vs. Frequency.

#### 2.6 Chip Select Response

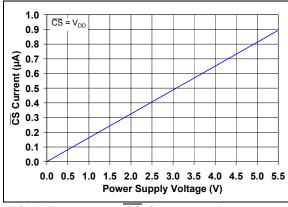
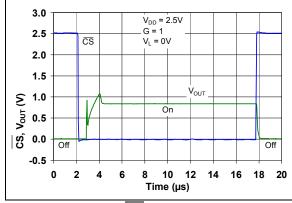
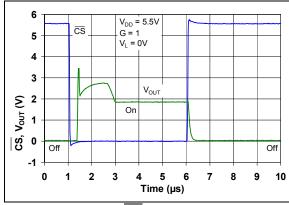


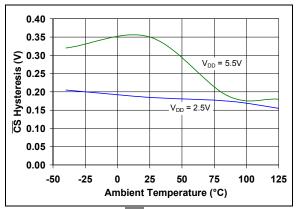
FIGURE 2-42: CS Current vs. Power Supply Voltage.



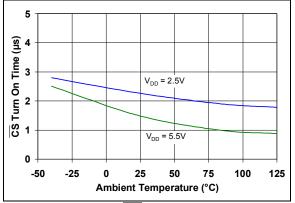
**FIGURE 2-43:**  $\overline{CS}$  and Output Voltages vs. Time with  $V_{DD}$  = 2.5V.



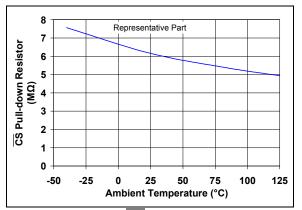
**FIGURE 2-44:**  $\overline{CS}$  and Output Voltages vs. Time with  $V_{DD}$  = 5.5V.



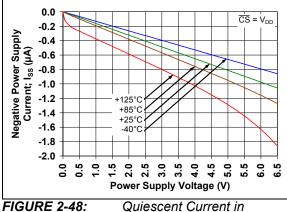
*FIGURE 2-45: CS Hysteresis vs. Ambient Temperature.* 



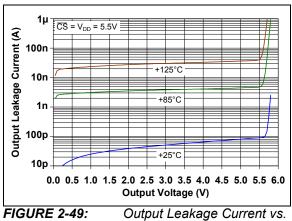
**FIGURE 2-46:** CS Turn On Time vs. Ambient Temperature.



**FIGURE 2-47:** CS's Pull-down Resistor (*R*<sub>PD</sub>) vs. Ambient Temperature.



Shutdown vs. Power Supply Voltage.



Output Voltage.

NOTES:

# 3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in Table 3-1.

# TABLE 3-1: PIN FUNCTION TABLE

MCF	9660	0 MCP661		I	MCP	662	MCI	P663	MCP664	MCF	P665	MCP669			
4x4 QFN	SOIC, TSSOP	SOIC	2x3 TDFN	SOT-23	MSOP, SOIC	DFN	SOIC	SOT-23	SOIC, TSSOP	<b>JOSM</b>	DFN	4x4 QFN	Symbol	Description	
5	6	2	2	4	2	2	2	4	2	2	2	1	V <sub>IN</sub> -, V <sub>INA</sub> -	Inverting Input (op amp A)	
4	5	3	3	3	3	3	3	3	3	3	3	2	V <sub>IN</sub> +, V <sub>INA</sub> +	Non-inverting Input (op amp A)	
3	4	7	7	5	8	8	7	6	4	10	10	3	V <sub>DD</sub>	Positive Power Supply	
10	10				5	5	_		5	7	7	4	V <sub>INB</sub> +	Non-inverting Input (op amp B)	
9	9	_	_	_	6	6	_	_	6	8	8	5	V <sub>INB</sub> -	Inverting Input (op amp B)	
8	8	_	_	_	7	7	_	_	7	9	9	6	V <sub>OUTB</sub>	Output (op amp B)	
_		_	_	_	_	_	_	_	_	_	—	7	CSBC	Chip Select Digital Input (op amps B and C	
14	14	_	_	_	_	_	_	_	8	_	—	8	V <sub>OUTC</sub>	Output (op amp C)	
13	13	—	_	_	_	_	_	_	9	_	—	9	V <sub>INC</sub> -	Inverting Input (op amp C)	
12	12	—	_	_	_	_	_	_	10	_	—	10	V <sub>INC</sub> +	Non-inverting Input (op amp C)	
11	11	4	4	2	4	4	4	2	11	4	4	11	V <sub>SS</sub>	Negative Power Supply	
—	_	—	-	—	—	—	_	—	12	-	—	12	V <sub>IND</sub> +	Inverting Input (op amp D)	
—	_	_		—	_	—		—	13		—	13	V <sub>IND</sub> -	Inverting Input (op amp D)	
—	_			_	_	—		_	14		—	14	V <sub>OUTD</sub>	Output (op amp D)	
_	_			_	_	_		_	—		_	15	CSAD	Chip Select Digital Input (op amps A and D	
6	7	6	6	1	1	1	6	1	1	1	1	16	V <sub>OUT</sub> , V <sub>OUTA</sub>	Output (op amp A)	
17	_	—		—	—	9	_	_	_		11	17	EP	Exposed Thermal Pad (EP); must be connected to $V_{SS}$	
		_			_	_	8	5	_	5	5		CS, CSA	Chip Select Digital Input (op amp A)	
_	—	_		—	—	_	_	—	—	6	6		CSB	Chip Select Digital Input (op amp B)	
1, 2, 7, 15, 16	1, 2, 3	1, 5, 8	1,2	—	_	—	1, 5	—	—	—	—	—	NC	No Internal Connection	

MCP660/1/2/3/4/5/9

# 3.1 Analog Outputs

The analog output pins ( $V_{OUT}$ ) are low-impedance voltage sources.

# 3.2 Analog Inputs

The non-inverting and inverting inputs (V\_{IN}+, V\_{IN}-, ...) are high-impedance CMOS inputs with low bias currents.

# 3.3 Power Supply Pins

The positive power supply ( $V_{DD}$ ) is 2.5V to 5.5V higher than the negative power supply ( $V_{SS}$ ). For normal operation, the other pins are between  $V_{SS}$  and  $V_{DD}$ .

Typically, these parts are used in a single (positive) supply configuration. In that case,  $V_{SS}$  is connected to ground and  $V_{DD}$  is connected to the supply.  $V_{DD}$  will need bypass capacitors.

# 3.4 Chip Select Digital Input (CS)

The input  $(\overline{CS})$  is a CMOS, Schmitt-triggered input that places the part into a Low Power mode of operation.

# 3.5 Exposed Thermal Pad (EP)

There is an internal connection between the exposed thermal pad (EP) and the  $V_{SS}$  pin; they must be connected to the same potential on the printed circuit board (PCB).

This pad can be connected to a PCB ground plane to provide a larger heat sink. This improves the package thermal resistance ( $\theta_{JA}$ ).

# 4.0 APPLICATIONS

The MCP660/1/2/3/4/5/9 family is manufactured using the Microchip state-of-the-art CMOS process. It is designed for low-cost, low-power and high-speed applications. Its low supply voltage, low quiescent current and wide bandwidth make the MCP660/1/2/3/4/5/9 ideal for battery-powered applications.

## 4.1 Input

#### 4.1.1 PHASE REVERSAL

The input devices are designed to not exhibit phase inversion when the input pins exceed the supply voltages. Figure 2-39 shows an input voltage exceeding both supplies with no phase inversion.

#### 4.1.2 INPUT VOLTAGE AND CURRENT LIMITS

The electrostatic discharge (ESD) protection on the inputs can be depicted as shown in Figure 4-1. This structure was chosen to protect the input transistors, and to minimize input bias current ( $I_B$ ). The input ESD diodes clamp the inputs when they try to go more than one diode drop below  $V_{SS}$ . They also clamp any voltages that go too far above  $V_{DD}$ ; their breakdown voltage is high enough to allow normal operation, and low enough to bypass quick ESD events within the specified limits.

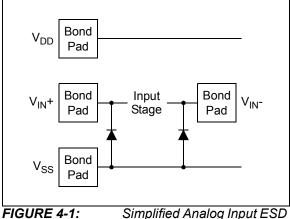
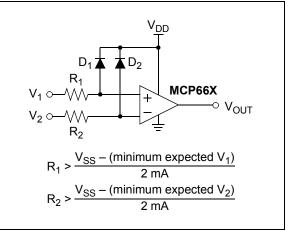


FIGURE 4-1: Simplified Analog Input ESD Structures.

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the currents (and voltages) at the input pins (see **Section 1.1 "Absolute Maximum Ratings †**"). Figure 4-2 shows the recommended approach to protecting these inputs.

The internal ESD diodes prevent the input pins (V<sub>IN</sub>+ and V<sub>IN</sub>-) from going too far below ground, and the resistors R<sub>1</sub> and R<sub>2</sub> limit the possible current drawn out of the input pins. Diodes D<sub>1</sub> and D<sub>2</sub> prevent the input pins (V<sub>IN</sub>+ and V<sub>IN</sub>-) from going too far above V<sub>DD</sub>, and dump any currents onto V<sub>DD</sub>.

When implemented as shown, resistors  $R_1$  and  $R_2$  also limit the current through  $D_1$  and  $D_2$ .



# **FIGURE 4-2:** Protecting the Analog Inputs.

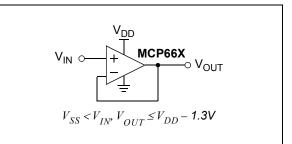
It is also possible to connect the diodes to the left of the resistors R<sub>1</sub> and R<sub>2</sub>. If they are, the currents through the diodes D<sub>1</sub> and D<sub>2</sub> need to be limited by some other mechanism. The resistors then serve as in-rush current limiters; the DC current into the input pins (V<sub>IN</sub>+ and V<sub>IN</sub>-) should be very small.

A significant amount of current can flow out of the inputs (through the ESD diodes) when the Common mode voltage ( $V_{CM}$ ) is below ground ( $V_{SS}$ ); see Figure 2-13. Applications that are high impedance may need to limit the usable voltage range.

#### 4.1.3 NORMAL OPERATION

The input stage of the MCP660/1/2/3/4/5/9 op amps uses a differential PMOS input stage. It operates at low Common mode input voltages (V<sub>CM</sub>), with V<sub>CM</sub> between V<sub>SS</sub> – 0.3V and V<sub>DD</sub> – 1.3V. To ensure proper operation, the input offset voltage (V<sub>OS</sub>) is measured at both V<sub>CM</sub> = V<sub>SS</sub> – 0.3V and V<sub>DD</sub> – 1.3V. See Figure 2-5 and Figure 2-6 for temperature effects.

When operating at very low non-inverting gains, the output voltage is limited at the top by the V<sub>CM</sub> range (<V<sub>DD</sub> – 1.3V); see Figure 4-3.



**FIGURE 4-3:** Unity Gain Voltage Limitations for Linear Operation.

# 4.2 Rail-to-Rail Output

#### 4.2.1 MAXIMUM OUTPUT VOLTAGE

The Maximum Output Voltage (see Figure 2-16 and Figure 2-17) describes the output range for a given load. For example, the output voltage swings to within 50 mV of the negative rail with a 1 k $\Omega$  load tied to V<sub>DD</sub>/2.

#### 4.2.2 OUTPUT CURRENT

Figure 4-4 shows the possible combinations of output voltage ( $V_{OUT}$ ) and output current ( $I_{OUT}$ ), when  $V_{DD}$  = 5.5V.

 $\mathsf{I}_{\mathsf{OUT}}$  is positive when it flows out of the op amp into the external circuit.

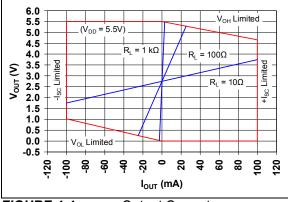


FIGURE 4-4:

Output Current.

#### 4.2.3 POWER DISSIPATION

Since the output short circuit current  $(I_{SC})$  is specified at ±90 mA (typical), these op amps are capable of both delivering and dissipating significant power.

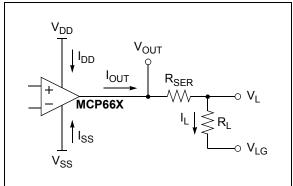


FIGURE 4-5: Diagram for Power Calculations.

Figure 4-5 shows the power calculations used for a single op amp:

- $R_{SER}$  is  $0\Omega$  in most applications, and can be used to limit  $I_{OUT}$
- V<sub>OUT</sub> is the op amp's output voltage.
- V<sub>L</sub> is the voltage at the load.
- V<sub>LG</sub> is the load's ground point.
- V<sub>SS</sub> is usually ground (0V).

The input currents are assumed to be negligible. The currents shown in Figure 4-5 can be approximated using Equation 4-1:

#### **EQUATION 4-1:**

$$\begin{split} I_{OUT} = I_L = \frac{V_{OUT} - V_{LG}}{R_{SER} + R_L} \\ I_{DD} \approx I_Q + max(0, I_{OUT}) \\ I_{SS} \approx -I_Q + min(0, I_{OUT}) \end{split}$$
 Where:

I<sub>Q</sub> = quiescent supply current

The instantaneous op amp power ( $P_{OA}(t)$ ),  $R_{SER}$  power ( $P_{RSER}(t)$ ) and load power ( $P_L(t)$ ) are calculated in Equation 4-2:

#### **EQUATION 4-2:**

$$P_{OA}(t) = I_{DD} (V_{DD} - V_{OUT}) + I_{SS} (V_{SS} - V_{OUT})$$
$$P_{RSER}(t) = I_{OUT}^2 R_{SER}$$
$$P_L(t) = I_L^2 R_L$$

The maximum op amp power, for resistive loads, occurs when  $V_{OUT}$  is halfway between  $V_{DD}$  and  $V_{LG}$  or halfway between  $V_{SS}$  and  $V_{LG}.$ 

#### EQUATION 4-3:

$$P_{OAmax} \leq \frac{max^2(V_{DD} - V_{LG} - V_{SS})}{4(R_{SER} + R_L)}$$

The maximum ambient to junction temperature rise  $(\Delta T_{JA})$  and junction temperature  $(T_J)$  can be calculated using P<sub>OAmax</sub>, ambient temperature  $(T_A)$ , the package thermal resistance  $(\theta_{JA} - \text{found in Table 1-4})$ , and the number of op amps in the package (assuming equal power dissipations), as shown in Equation 4-4:

#### **EQUATION 4-4:**

$$\Delta T_{JA} = P_{OA}(t) \ \theta_{JA} \le n \ P_{OAmax} \theta_{JA}$$
$$T_J = T_A + \Delta T_{IA}$$

Where:

n = number of op amps in package (1, 2)

The power derating across temperature for an op amp in a particular package can be easily calculated (assuming equal power dissipations):

#### **EQUATION 4-5:**

$$P_{OAmax} \leq \frac{T_{Jmax} - T_A}{n \ \theta_{JA}}$$
  
Where:  
$$T_{Jmax} = absolute max. junction temperature$$

Several techniques are available to reduce  $\Delta T_{JA}$  for a given  $P_{OAmax}$ :

- Lower  $\theta_{JA}$ 
  - Use another package
  - PCB layout (ground plane, etc.)
  - Heat sinks and air flow
- Reduce P<sub>OAmax</sub>
  - Increase R<sub>L</sub>
  - Limit I<sub>OUT</sub> (using R<sub>SER</sub>)
  - Decrease V<sub>DD</sub>

# 4.3 Distortion

Differential gain (DG) and differential phase (DP) refer to the non-linear distortion produced by an NTSC or a phase-alternating line (PAL) video component. Table 1-2 and Figure 2-34 show the typical performance of the MCP661, configured as a gain of +2 amplifier (see Figure 4-10), when driving one back-matched video load (150 $\Omega$ , for 75 $\Omega$  cable). Microchip tests use a sine wave at NTSC's color sub-carrier frequency of 3.58 MHz, with a 0.286V<sub>P-P</sub> magnitude. The DC input voltage is changed over a +0.7V range (positive video) or a -0.7V range (negative video).

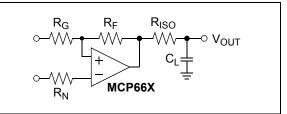
DG is the peak-to-peak change in the AC gain magnitude (color hue), as the DC level (luminance) is changed, in percentile units (%). DP is the peak-topeak change in the AC gain phase (color saturation), as the DC level (luminance) is changed, in degree (°) units.

#### 4.4 Improving Stability

#### 4.4.1 CAPACITIVE LOADS

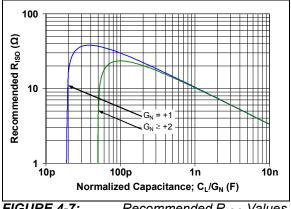
Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the phase margin (stability) of the feedback loop decreases and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. A unity gain buffer (G = +1) is the most sensitive to capacitive loads, though all gains show the same general behavior.

When driving large capacitive loads with these op amps (e.g., >20 pF when G = +1), a small series resistor at the output ( $R_{ISO}$  in Figure 4-6) improves the phase margin of the feedback loop by making the output load resistive at higher frequencies. The bandwidth generally will be lower than bandwidth without the capacitive load.



#### **FIGURE 4-6:** Output Resistor, R<sub>ISO</sub> Stabilizes Large Capacitive Loads.

Figure 4-7 gives recommended  $R_{ISO}$  values for different capacitive loads and gains. The x-axis is the normalized load capacitance ( $C_L/G_N$ ), where  $G_N$  is the circuit's noise gain. For non-inverting gains,  $G_N$  and the Signal Gain are equal. For inverting gains,  $G_N$  is 1+|Signal Gain| (e.g., -1 V/V gives  $G_N$  = +2 V/V).



**FIGURE 4-7:** Recommended R<sub>ISO</sub> Values for Capacitive Loads.

After selecting  $R_{\rm ISO}$  for the circuit, double-check the resulting frequency response peaking and step response overshoot. Modify the value of  $R_{\rm ISO}$  until the response is reasonable. Bench evaluation and simulations with the MCP660/1/2/3/4/5/9 SPICE macro model are helpful.

# 4.4.2 GAIN PEAKING

Figure 4-8 shows an op amp circuit that represents non-inverting amplifiers ( $V_M$  is a DC voltage and  $V_P$  is the input) or inverting amplifiers ( $V_P$  is a DC voltage and  $V_M$  is the input). The capacitances  $C_N$  and  $C_G$  represent the total capacitance at the input pins; they include the op amp's Common mode input capacitance ( $C_{CM}$ ), board parasitic capacitance and any capacitor placed in parallel.

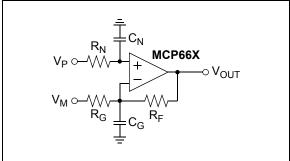
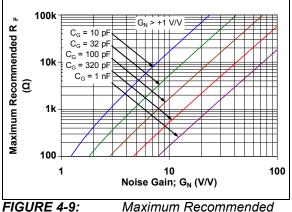


FIGURE 4-8: Amplifier with Parasitic Capacitance.

 $C_G$  acts in parallel with  $R_G$  (except for a gain of +1 V/V), which causes an increase in gain at high frequencies.  $C_G$  also reduces the phase margin of the feedback loop, which becomes less stable. This effect can be reduced by either reducing  $C_G$  or  $R_F$ .

 $C_N$  and  $R_N$  form a low-pass filter that affects the signal at  $V_P$ . This filter has a single real pole at  $1/(2\pi R_N C_N)$ .

The largest value of R<sub>F</sub> that should be used, depends on noise gain (see G<sub>N</sub> in **Section 4.4.1 "Capacitive Loads**"), C<sub>G</sub> and the open-loop gain's phase shift. Figure 4-9 shows the maximum recommended R<sub>F</sub> for several C<sub>G</sub> values. Some applications may modify these values to reduce either output loading or gain peaking (step response overshoot).



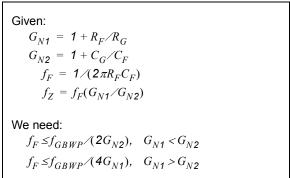
**FIGURE 4-9:** Maximum Recommended  $R_F$  vs. Gain.

Figure 2-35 and Figure 2-36 show the small signal and large signal step responses at G = +1 V/V. The unity gain buffer usually has  $R_F = 0\Omega$  and  $R_G$  open.

Figure 2-37 and Figure 2-38 show the small signal and large signal step responses at G = -1 V/V. Since the noise gain is 2 V/V and  $C_G \approx 10$  pF, the resistors were chosen to be  $R_F = R_G = 401\Omega$  and  $R_N = 200\Omega$ .

It is also possible to add a capacitor (C<sub>F</sub>) in parallel with R<sub>F</sub> to compensate for the destabilizing effect of C<sub>G</sub>. This makes it possible to use larger values of R<sub>F</sub>. The conditions for stability are summarized in Equation 4-6.

# **EQUATION 4-6:**



# 4.5 MCP663 and MCP665 Chip Select

The MCP663 is a single amplifier with Chip Select (CS). When CS is pulled high, the supply current drops to 1  $\mu$ A (typical) and flows through the CS pin to V<sub>SS</sub>. When this happens, the amplifier output is put into a high-impedance state. By pulling CS low, the amplifier is enabled. The CS pin has an internal 5 MΩ (typical) pulldown resistor connected to V<sub>SS</sub>, so it will go low if the CS pin is left floating. Figure 1-1, Figure 2-43 and Figure 2-44 show the output voltage and supply current response to a CS pulse.

The MCP665 is a dual amplifier with two  $\overline{\text{CS}}$  pins;  $\overline{\text{CSA}}$  controls op amp A, and  $\overline{\text{CSB}}$  controls op amp B. These op amps are controlled independently, with an enabled quiescent current ( $I_Q$ ) of 6 mA/amplifier (typical) and a disabled  $I_Q$  of 1 µA/amplifier (typical). The  $I_Q$  seen at the supply pins is the sum of the two op amps'  $I_Q$ ; the typical value for the  $I_Q$  of the MCP665 will be 2 µA, 6 mA or 12 mA when there are 0, 1 or 2 amplifiers enabled, respectively.

# 4.6 Power Supply

With this family of operational amplifiers, the power supply pin (V<sub>DD</sub> for single supply) should have a local bypass capacitor (i.e., 0.01  $\mu$ F to 0.1  $\mu$ F) within 2 mm for good high frequency performance. Surface mount, multilayer ceramic capacitors, or their equivalent, should be used.

These op amps require a bulk capacitor (i.e.,  $2.2 \ \mu$ F or larger) within 50 mm to provide large, slow currents. Tantalum capacitors, or their equivalent, may be a good choice. This bulk capacitor can be shared with other nearby analog parts as long as crosstalk through the power supplies does not prove to be a problem.

## 4.7 High Speed PCB Layout

These op amps are fast enough that a little extra care in the printed circuit board (PCB) layout can make a significant difference in performance. Good PC board layout techniques will help you achieve the performance shown in the specifications and typical performance curves; it will also help to minimize electromagnetic compatibility (EMC) issues.

Use a solid ground plane. Connect the bypass local capacitor(s) to this plane with minimal length traces. This cuts down inductive and capacitive crosstalk.

Separate digital from analog, low speed from high speed, and low power from high power. This will reduce interference.

Keep sensitive traces short and straight. Separate them from interfering components and traces. This is especially important for high frequency (low rise time) signals.

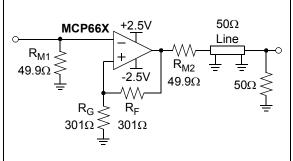
Sometimes, it helps to place guard traces next to victim traces. They should be on both sides of the victim trace, and as close as possible. Connect guard traces to ground plane at both ends, and in the middle for long traces.

Use coax cables, or low inductance wiring, to route signal and power to and from the PCB. Mutual and self inductance of power wires is often a cause of crosstalk and unusual behavior.

# 4.8 Typical Applications

#### 4.8.1 50Ω LINE DRIVER

Figure 4-10 shows the MCP661 driving a 50 $\Omega$  line. The large output current (e.g., see Figure 2-18) makes it possible to drive a back-matched line (R<sub>M2</sub>, the 50 $\Omega$  line and the 50 $\Omega$  load at the far end) to more than ±2V (the load at the far end sees ±1V). It is worth mentioning that the 50 $\Omega$  line and the 50 $\Omega$  load at the far end together can be modeled as a simple 50 $\Omega$  resistor to ground.

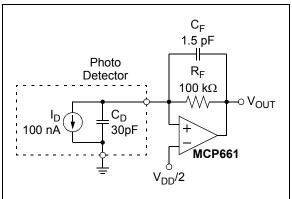


**FIGURE 4-10:**  $50 \Omega$  Line Driver.

The output headroom limits would be  $V_{OL} = -2.3V$  and  $V_{OH} = +2.3V$  (see Figure 2-16), leaving some design room for the ±2V signal. The open-loop gain (A<sub>OL</sub>) typically does not decrease significantly with a 100 $\Omega$  load (see Figure 2-11). The maximum power dissipated is about 48 mW (see Section 4.2.3 "Power Dissipation"), so the temperature rise (for the MCP661 in the SOIC-8 package) is under 8°C.

#### 4.8.2 OPTICAL DETECTOR AMPLIFIER

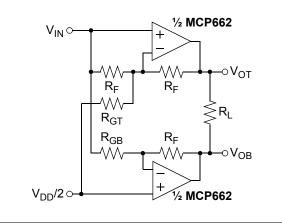
Figure 4-11 shows a transimpedance amplifier, using the MCP661 op amp, in a photo detector circuit. The photo detector is a capacitive current source. R<sub>F</sub> provides enough gain to produce 10 mV at V<sub>OUT</sub>. C<sub>F</sub> stabilizes the gain and limits the transimpedance bandwidth to about 1.1 MHz. The parasitic capacitance of R<sub>F</sub> (e.g., 0.2 pF for a 0805 SMD) acts in parallel with C<sub>F</sub>.



**FIGURE 4-11:** Transimpedance Amplifier for an Optical Detector.

#### 4.8.3 H-BRIDGE DRIVER

Figure 4-12 shows the MCP662 dual op amp used as an H-bridge driver. The load could be a speaker or a DC motor.





This circuit automatically makes the noise gains ( $G_N$ ) equal, when the gains are set properly, so that the frequency responses match well (in magnitude and in phase). Equation 4-7 shows how to calculate  $R_{GT}$  and  $R_{GB}$  so that both op amps have the same DC gains;  $G_{DM}$  needs to be selected first.

**EQUATION 4-7:** 

$$G_{DM} = \frac{V_{OT} - V_{OB}}{V_{IN} - V_{DD}/2} \ge 1 \text{ V/V}$$

$$R_{GT} = \frac{R_F}{(G_{DM}/2) - 1}$$

$$R_{GB} = \frac{R_F}{G_{DM}/2}$$

Equation 4-8 gives the resulting Common mode and Differential mode output voltages.

**EQUATION 4-8:** 

$$\frac{V_{OT} + V_{OB}}{2} = \frac{V_{DD}}{2}$$
$$V_{OT} - V_{OB} = G_{DM} \left( V_{IN} - \frac{V_{DD}}{2} \right)$$

# 5.0 DESIGN AIDS

Microchip provides the basic design aids needed for the MCP660/1/2/3/4/5/9 family of op amps.

# 5.1 SPICE Macro Model

The latest SPICE macro model for the MCP660/1/2/3/4/5/9 op amps is available on the Microchip web site at www.microchip.com. This model is intended to be an initial design tool that works well in the linear region of operation over the temperature range of the op amp. See the model file for information on its capabilities.

Bench testing is a very important part of any design and cannot be replaced with simulations. Also, simulation results using this macro model need to be validated, by comparing them to the data sheet specifications and characteristic curves.

# 5.2 FilterLab<sup>®</sup> Software

Microchip's FilterLab<sup>®</sup> software is an innovative software tool that simplifies analog active filter (using op amps) design. Available at no cost from the Microchip web site at www.microchip.com/filterlab, the Filter-Lab design tool provides full schematic diagrams of the filter circuit with component values. It also outputs the filter circuit in SPICE format, which can be used with the macro model to simulate actual filter performance.

# 5.3 Microchip Advanced Part Selector (MAPS)

MAPS is a software tool that helps efficiently identify Microchip devices that fit a particular design requirement. Available at no cost from the Microchip web site at www.microchip.com/maps, the MAPS is an overall selection tool for Microchip's product portfolio that includes Analog, Memory, MCUs and DSCs. Using this tool, a filter can be defined to sort features for a parametric search of device, and export side-by-side technical comparison reports. Helpful links are also provided for data sheets, purchase and sampling of Microchip parts.

# 5.4 Analog Demonstration and Evaluation Boards

Microchip offers a broad spectrum of analog demonstration and evaluation boards that are designed to help customers achieve faster time to market. For a complete listing of these boards and their corresponding user's guides and technical information, visit the Microchip web site at www.microchip.com/analog tools.

Some boards that are especially useful are:

- MCP6XXX Amplifier Evaluation Board 1, part number: MCP6XXXEV-AMP1
- MCP6XXX Amplifier Evaluation Board 2, part number: MCP6XXXEV-AMP2
- MCP6XXX Amplifier Evaluation Board 3, part number: MCP6XXXEV-AMP3
- MCP6XXX Amplifier Evaluation Board 4, part number: MCP6XXXEV-AMP3
- Active Filter Demo Board Kit, part number: MCP6XXXDM-FLTR
- 8-Pin SOIC/MSOP/TSSOP/DIP Evaluation Board, part number: SOIC8EV
- MCP661 Line Driver Demo Board, part number: MCP661DM-LD

# 5.5 Design and Application Notes

The following Microchip Analog Design Note and Application Notes are recommended as supplemental reference resources. They are available on the Microchip web site at www.microchip.com/appnotes.

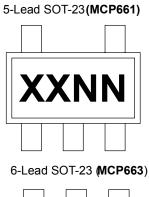
- ADN003: "Select the Right Operational Amplifier for your Filtering Circuits", DS21821
- AN722: "Operational Amplifier Topologies and DC Specifications", DS00722
- AN723: "Operational Amplifier AC Specifications and Applications", DS00723
- AN884: "Driving Capacitive Loads With Op Amps", DS00884
- AN990: "Analog Sensor Conditioning Circuits An Overview", DS00990
- AN1228: "Op Amp Precision Design: Random Noise", DS01228

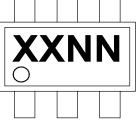
Some of these application notes, and others, are listed in the *"Signal Chain Design Guide"*, DS21825.

NOTES:

# 6.0 PACKAGING INFORMATION

# 6.1 Package Marking Information





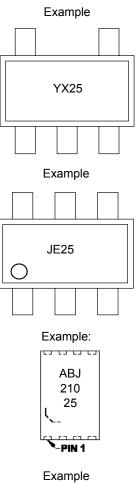
8-Lead TDFN (2 x 3)(MCP661)

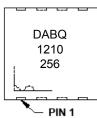


8-Lead DFN (3x3)(MCP662)



Device	Code
MCP662T-E/MF	DABQ
Note: Applies to	8-Lead 3x3 DFN





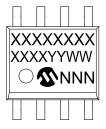
Legend	: XXX Y YY WW NNN @3 *	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.
	be carried	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available for customer-specific information.

# Package Marking Information (Continued)

8-Lead MSOP (3x3 mm) (MCP662)



8-Lead SOIC (150 mil) (MCP661, MCP662, MCP663)



10-Lead DFN (3×3) (MCP665)



Device	Code				
MCP665	BAFD				
Note: Applica to 10 Load 2v2 DEN					

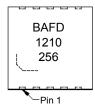
Note: Applies to 10-Lead 3x3 DFN



Example:



Example



Example:

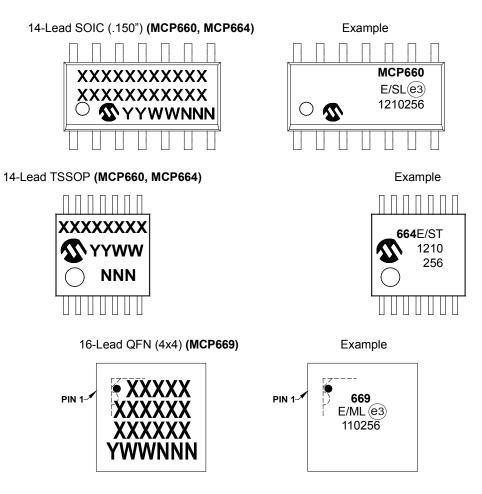


Legend	I: XXX Y YY WW NNN <u>@</u> 3	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn)
Note:	be carrie	This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package. nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for customer-specific information.

10-Lead MSOP (MCP665)



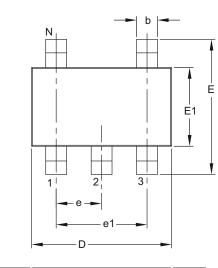
# Package Marking Information (Continued)

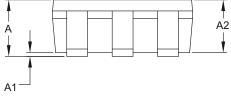


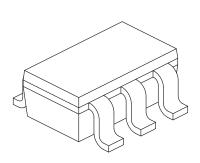
Legend	d: XXX	Customer-specific information		
	Y	Year code (last digit of calendar year)		
	YY Year code (last 2 digits of calendar year)			
	WW Week code (week of January 1 is week '01')			
	NNN Alphanumeric traceability code			
	(e3)	Pb-free JEDEC designator for Matte Tin (Sn)		
	*	This package is Pb-free. The Pb-free JEDEC designator ( $(e_3)$ )		
		can be found on the outer packaging for this package.		
Note:	In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.			

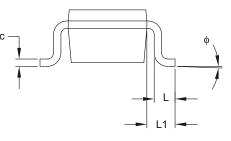
# 5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging









	Units	MILLIMETERS		
	Dimension Limits	MIN	NOM	MAX
Number of Pins	N	5		
Lead Pitch	e	0.95 BSC		
Outside Lead Pitch	e1	1.90 BSC		
Overall Height	А	0.90	-	1.45
Molded Package Thickness	A2	0.89	-	1.30
Standoff	A1	0.00	-	0.15
Overall Width	E	2.20	-	3.20
Molded Package Width	E1	1.30	-	1.80
Overall Length	D	2.70	-	3.10
Foot Length	L	0.10	_	0.60
Footprint	L1	0.35	_	0.80
Foot Angle	φ	0°	-	30°
Lead Thickness	С	0.08	-	0.26
Lead Width	b	0.20	-	0.51

#### Notes:

1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.

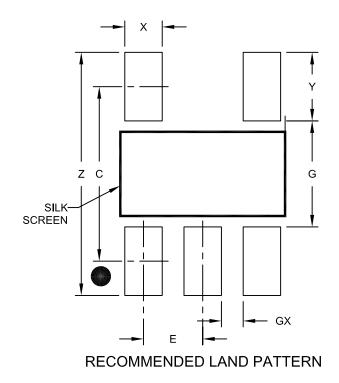
2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-091B

# 5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	E	0.95 BSC			
Contact Pad Spacing	С		2.80		
Contact Pad Width (X5)	X			0.60	
Contact Pad Length (X5)	Y			1.10	
Distance Between Pads	G	1.70			
Distance Between Pads	GX	0.35			
Overall Width	Z			3.90	

Notes:

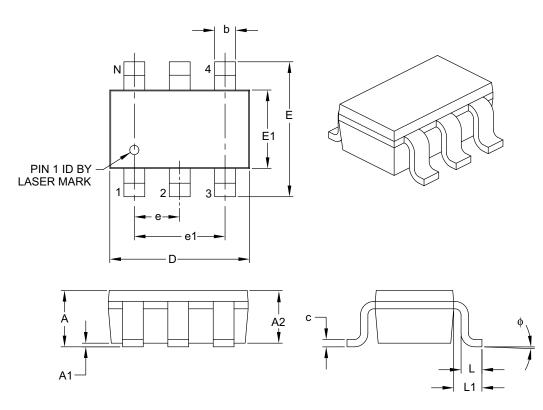
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2091A

# 6-Lead Plastic Small Outline Transistor (CHY) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units		MILLIMETERS			
	Dimension Limits	MIN	NOM	MAX		
Number of Pins	N	6				
Pitch	е	0.95 BSC				
Outside Lead Pitch	e1	1.90 BSC				
Overall Height	А	0.90	-	1.45		
Molded Package Thickness	A2	0.89	-	1.30		
Standoff	A1	0.00	-	0.15		
Overall Width	E	2.20	-	3.20		
Molded Package Width	E1	1.30	-	1.80		
Overall Length	D	2.70	-	3.10		
Foot Length	L	0.10	-	0.60		
Footprint	L1	0.35	-	0.80		
Foot Angle	φ	0°	-	30°		
Lead Thickness	С	0.08	-	0.26		
Lead Width	b	0.20	-	0.51		

#### Notes:

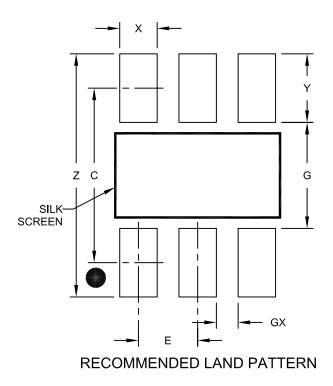
- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-028B

# 6-Lead Plastic Small Outline Transistor (CHY) [SOT-23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS				
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	Pitch E		0.95 BSC		
Contact Pad Spacing	С		2.80		
Contact Pad Width (X6)	X			0.60	
Contact Pad Length (X6)	Y			1.10	
Distance Between Pads	G	1.70			
Distance Between Pads	GX	0.35			
Overall Width	Z			3.90	

Notes:

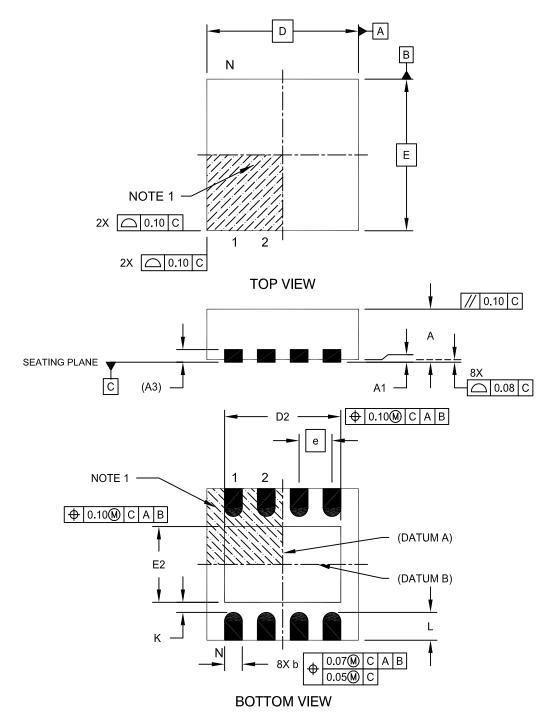
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2028A

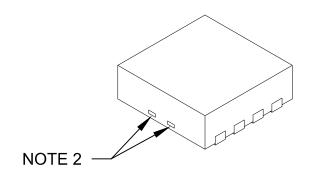
# 8-Lead Plastic Dual Flat, No Lead Package (MF) - 3x3x0.9mm Body [DFN]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-062C Sheet 1 of 2

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units			S	
Dimensior	Dimension Limits		NOM	MAX	
Number of Pins	N		8		
Pitch	е		0.65 BSC	_	
Overall Height	A	0.80	0.90	1.00	
Standoff	A1	0.00	0.02	0.05	
Contact Thickness	A3	0.20 REF			
Overall Length	D		3.00 BSC		
Exposed Pad Width	E2	1.34	-	1.60	
Overall Width	E		3.00 BSC		
Exposed Pad Length	D2	1.60	-	2.40	
Contact Width	b	0.25	0.30	0.35	
Contact Length	L	0.20	0.30	0.55	
Contact-to-Exposed Pad	K	0.20	-	-	

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Package may have one or more exposed tie bars at ends.

3. Package is saw singulated

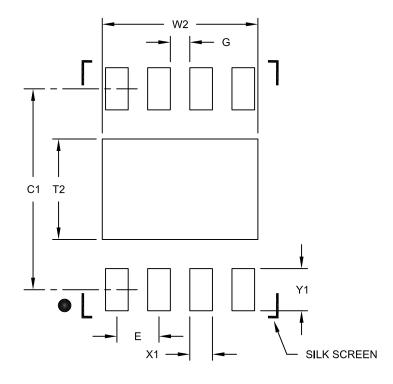
4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-062C Sheet 2 of 2

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



## RECOMMENDED LAND PATTERN

Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	E		0.65 BSC		
Optional Center Pad Width	W2			2.40	
Optional Center Pad Length	T2			1.55	
Contact Pad Spacing	C1		3.10		
Contact Pad Width (X8)	X1			0.35	
Contact Pad Length (X8)	Y1			0.65	
Distance Between Pads	G	0.30			

#### Notes:

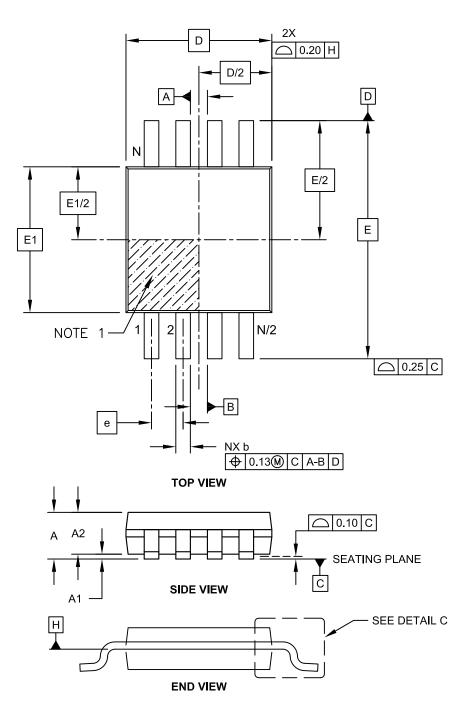
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2062B

# 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

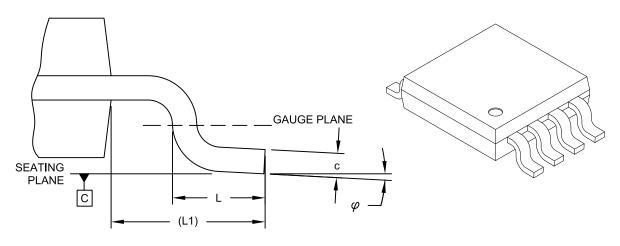
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-111C Sheet 1 of 2

## 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



DETAIL C

	Ν	MILLIMETERS			
Dimensio	Dimension Limits		NOM	MAX	
Number of Pins	Ν		8		
Pitch	е		0.65 BSC		
Overall Height	А	-	-	1.10	
Molded Package Thickness	A2	0.75	0.85	0.95	
Standoff	A1	0.00	-	0.15	
Overall Width	Е	4.90 BSC			
Molded Package Width	E1	3.00 BSC			
Overall Length	D		3.00 BSC		
Foot Length	L	0.40	0.60	0.80	
Footprint	L1	0.95 REF			
Foot Angle	φ	0°	-	8°	
Lead Thickness	С	0.08	-	0.23	
Lead Width	b	0.22	-	0.40	

#### Notes:

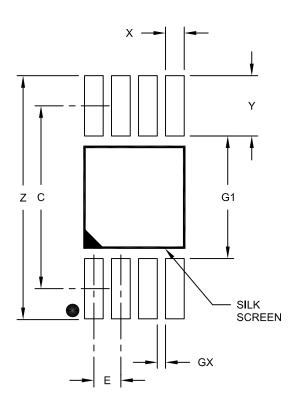
1. Pin 1 visual index feature may vary, but must be located within the hatched area.

- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
   Dimensioning and tolerancing per ASME Y14.5M.
  - Dimensioning and tolerancing per ASME Y14.5M. BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-111C Sheet 2 of 2

#### 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



## **RECOMMENDED LAND PATTERN**

	Units		MILLIMETERS		
Dimensio	Dimension Limits		NOM	MAX	
Contact Pitch	E	E 0.65 BSC			
Contact Pad Spacing	С		4.40		
Overall Width	Z			5.85	
Contact Pad Width (X8)	X1			0.45	
Contact Pad Length (X8)	Y1			1.45	
Distance Between Pads	G1	2.95			
Distance Between Pads	GX	0.20			

Notes:

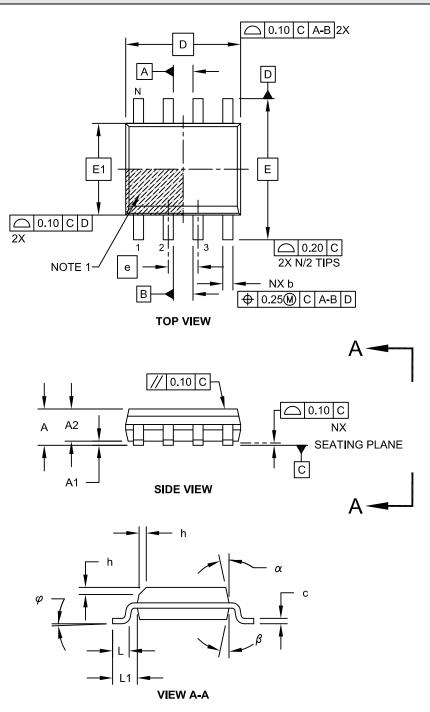
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2111A

#### 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

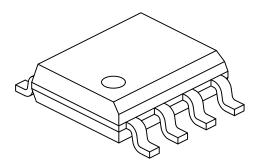
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-057C Sheet 1 of 2

#### 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	N	MILLIMETERS			
Dimensior	n Limits	MIN	NOM	MAX	
Number of Pins	N		8		
Pitch	е		1.27 BSC		
Overall Height	A	-	-	1.75	
Molded Package Thickness	A2	1.25	-	-	
Standoff §	A1	0.10	-	0.25	
Overall Width	E	6.00 BSC			
Molded Package Width	E1	3.90 BSC			
Overall Length	D	4.90 BSC			
Chamfer (Optional)	h	0.25	-	0.50	
Foot Length	L	0.40	-	1.27	
Footprint	L1		1.04 REF		
Foot Angle	φ	0°	-	8°	
Lead Thickness	С	0.17 - 0.25			
Lead Width	b	0.31	-	0.51	
Mold Draft Angle Top	α	5°	-	15°	
Mold Draft Angle Bottom	β	5°	-	15°	

#### Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. § Significant Characteristic

3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.

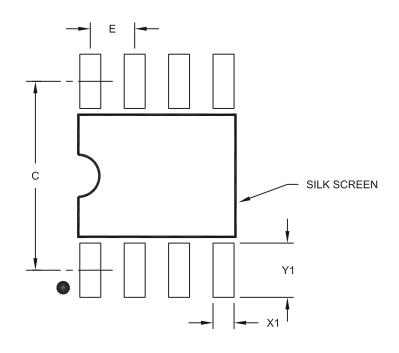
4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

## 8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	С		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

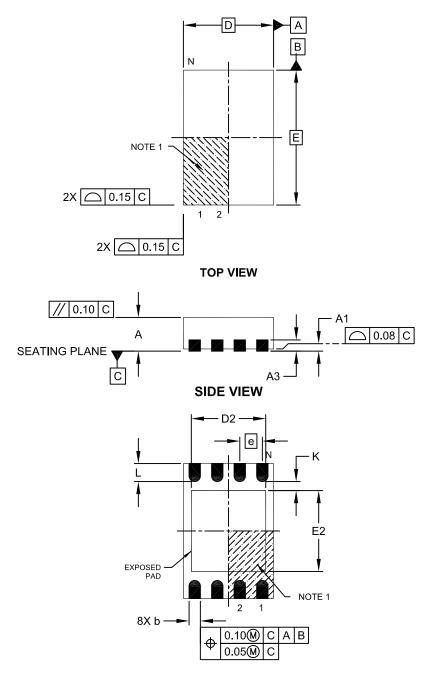
Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

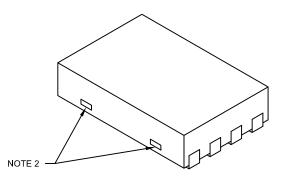
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### **BOTTOM VIEW**

Microchip Technology Drawing No. C04-129C Sheet 1 of 2

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	N	MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX	
Number of Pins	Ν		8		
Pitch	е		0.50 BSC		
Overall Height	Α	0.70	0.75	0.80	
Standoff	A1	0.00	0.02	0.05	
Contact Thickness	A3	0.20 REF			
Overall Length	D	2.00 BSC			
Overall Width	E		3.00 BSC		
Exposed Pad Length	D2	1.20	-	1.60	
Exposed Pad Width	E2	1.20	-	1.60	
Contact Width	b	0.20	0.25	0.30	
Contact Length	L	0.25	0.30	0.45	
Contact-to-Exposed Pad	К	0.20	-	-	

#### Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Package may have one or more exposed tie bars at ends.

3. Package is saw singulated

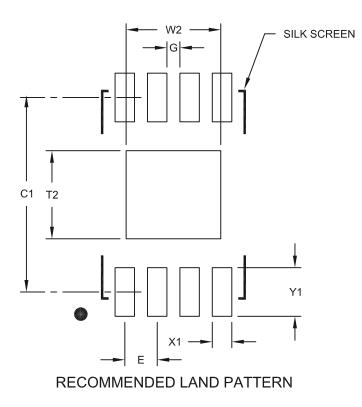
4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-129C Sheet 2 of 2

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	t Pitch E		0.50 BSC		
Optional Center Pad Width	W2			1.46	
Optional Center Pad Length	T2			1.36	
Contact Pad Spacing	C1		3.00		
Contact Pad Width (X8)	X1			0.30	
Contact Pad Length (X8)	Y1			0.75	
Distance Between Pads	G	0.20			

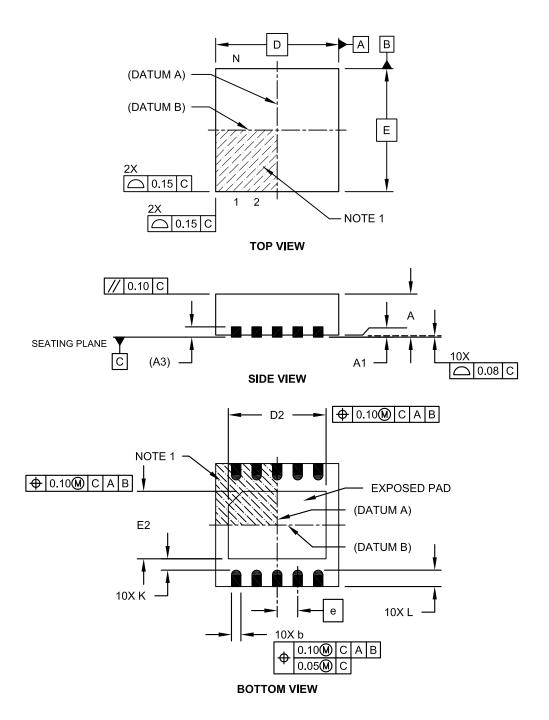
#### Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

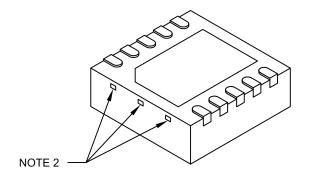
Microchip Technology Drawing No. C04-2129A

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-063C Sheet 1 of 2

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



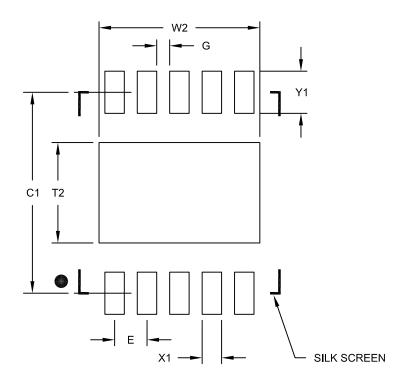
	Ν	MILLIMETERS		
Dimension	Dimension Limits		NOM	MAX
Number of Pins	Ν		10	
Pitch	е		0.50 BSC	
Overall Height	Α	0.80	0.90	1.00
Standoff	A1	0.00	0.02	0.05
Contact Thickness	A3	0.20 REF		
Overall Length	D	3.00 BSC		
Exposed Pad Length	D2	2.15	2.35	2.45
Overall Width	E		3.00 BSC	
Exposed Pad Width	E2	1.40	1.50	1.75
Contact Width	b	0.18	0.25	0.30
Contact Length	L	0.30	0.40	0.50
Contact-to-Exposed Pad	K	0.20	-	-

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package may have one or more exposed tie bars at ends.
- 3. Package is saw singulated.
- 4. Dimensioning and tolerancing per ASME Y14.5M.
  - BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-063C Sheet 2 of 2

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



## RECOMMENDED LAND PATTERN

Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	E		0.50 BSC		
Optional Center Pad Width	W2			2.48	
Optional Center Pad Length	T2			1.55	
Contact Pad Spacing	C1		3.10		
Contact Pad Width (X10)	X1			0.30	
Contact Pad Length (X10)	Y1			0.65	
Distance Between Pads	G	0.20			

#### Notes:

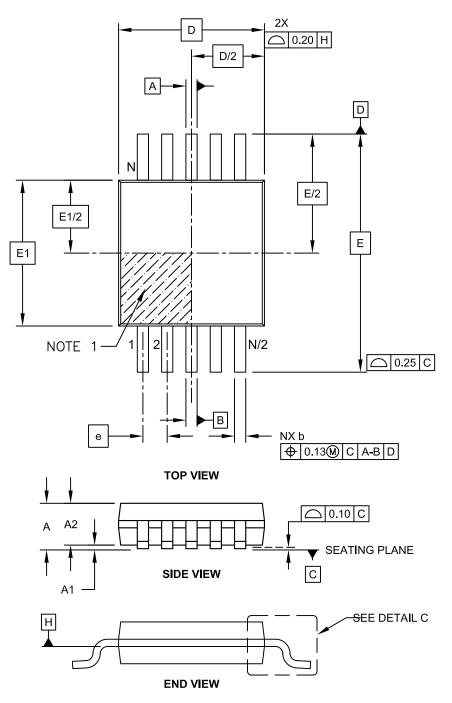
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2063B

## 10-Lead Plastic Micro Small Outline Package (UN) [MSOP]

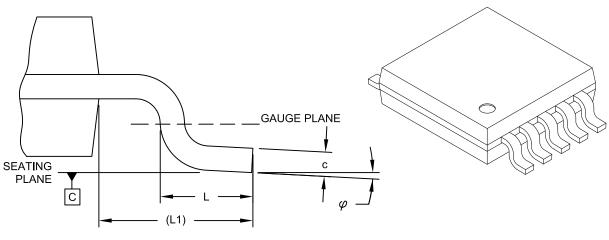
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-021C Sheet 1 of 2

#### 10-Lead Plastic Micro Small Outline Package (UN) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



DETAIL C

	Ν	MILLIMETERS			
Dimensior	n Limits	MIN	NOM	MAX	
Number of Pins	N		10		
Pitch	е		0.50 BSC		
Overall Height	A	-	-	1.10	
Molded Package Thickness	A2	0.75	0.85	0.95	
Standoff	A1	0.00	-	0.15	
Overall Width	E	4.90 BSC			
Molded Package Width	E1		3.00 BSC		
Overall Length	D		3.00 BSC		
Foot Length	L	0.40	0.60	0.80	
Footprint	L1	0.95 REF			
Foot Angle	φ	0°	-	8°	
Lead Thickness	С	0.08	-	0.23	
Lead Width	b	0.15	-	0.33	

#### Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or

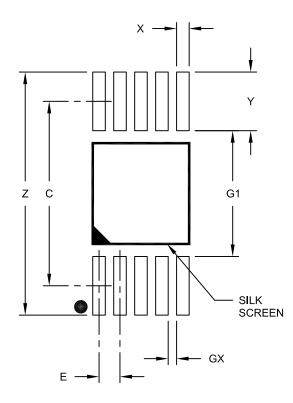
protrusions shall not exceed 0.15mm per side.

Dimensioning and tolerancing per ASME Y14.5M.
 BSC: Basic Dimension. Theoretically exact value shown without tolerances.
 REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-021C Sheet 2 of 2

## 10-Lead Plastic Micro Small Outline Package (UN) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



## RECOMMENDED LAND PATTERN

Units		MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX	
Contact Pitch	E		0.50 BSC		
Contact Pad Spacing	С		4.40		
Overall Width	Z			5.80	
Contact Pad Width (X10)	X1			0.30	
Contact Pad Length (X10)	Y1			1.40	
Distance Between Pads	G1	3.00			
Distance Between Pads	GX	0.20			

Notes:

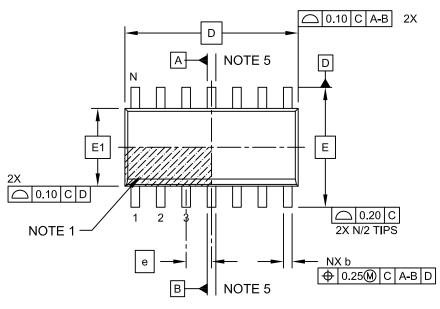
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

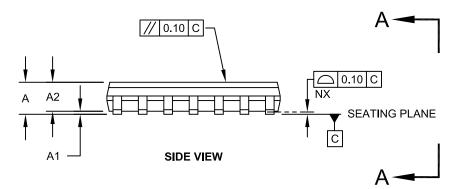
Microchip Technology Drawing No. C04-2021A

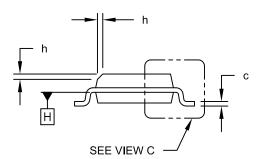
## 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



TOP VIEW



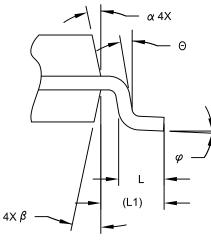


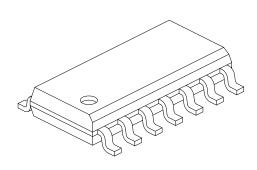




#### 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





VIEW C

	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		14	
Pitch	е		1.27 BSC	
Overall Height	A	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	8.65 BSC		
Chamfer (Optional)	h	0.25 - 0.50		
Foot Length	L	0.40	-	1.27
Footprint	L1	1.04 REF		
Lead Angle	Θ	0°	-	-
Foot Angle	φ	0°	-	8°
Lead Thickness	С	0.10	-	0.25
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5° - 15°		

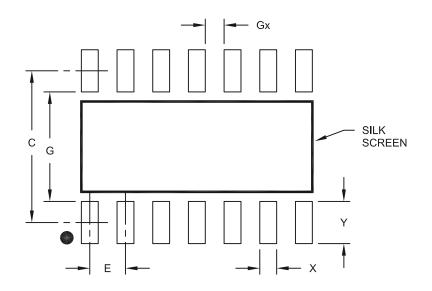
Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- 3. Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M
  - BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.
- 5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-065C Sheet 2 of 2

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



# RECOMMENDED LAND PATTERN

	Units		MILLIMETERS		
Dimensior	Dimension Limits		NOM	MAX	
Contact Pitch	E	1.27 BSC			
Contact Pad Spacing	С		5.40		
Contact Pad Width	X			0.60	
Contact Pad Length	Y			1.50	
Distance Between Pads	Gx	0.67			
Distance Between Pads	G	3.90			

Notes:

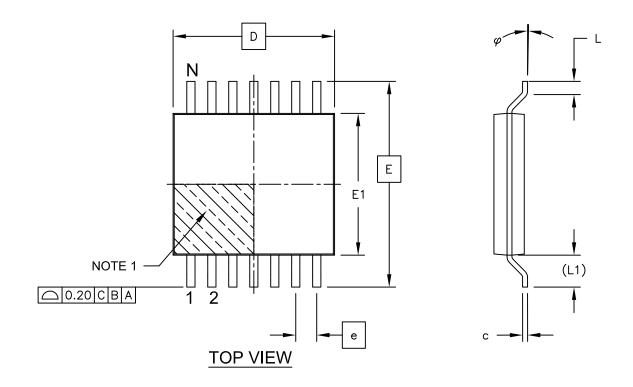
1. Dimensioning and tolerancing per ASME Y14.5M

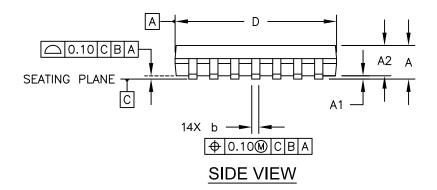
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2065A

# 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

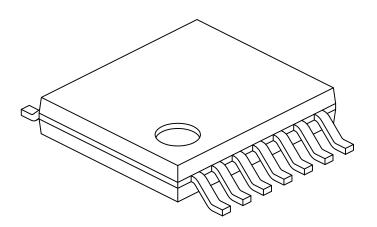




Microchip Technology Drawing C04-087C Sheet 1 of 2

#### 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimension	MIN	NOM	MAX	
Number of Pins	N	14		
Pitch	е		0.65 BSC	
Overall Height	Α	-	-	1.20
Molded Package Thickness	A2	0.80	1.00	1.05
Standoff	A1	0.05	-	0.15
Overall Width	Е	6.40 BSC		
Molded Package Width	E1	4.30 4.40 4.50		
Molded Package Length	D	4.90	5.00	5.10
Foot Length	L	0.45	0.60	0.75
Footprint	(L1)	1.00 REF		
Foot Angle	φ	0°	-	8°
Lead Thickness	С	0.09	-	0.20
Lead Width	b	0.19	-	0.30

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.

3. Dimensioning and tolerancing per ASME Y14.5M

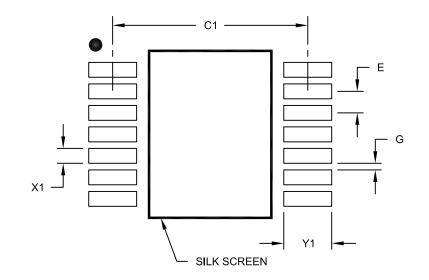
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-087C Sheet 2 of 2

#### 14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



# RECOMMENDED LAND PATTERN

Units		MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX	
Contact Pitch	E	0.65 BSC			
Contact Pad Spacing	C1		5.90		
Contact Pad Width (X14)	X1			0.45	
Contact Pad Length (X14)	Y1			1.45	
Distance Between Pads	G	0.20			

Notes:

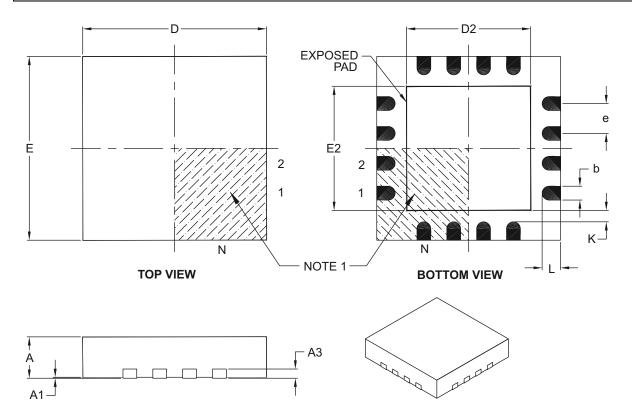
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2087A

## 16-Lead Plastic Quad Flat, No Lead Package (ML) – 4x4x0.9 mm Body [QFN]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	MILLIMETERS			
	Dimension Limits	MIN	NOM	MAX	
Number of Pins	N	16			
Pitch	e		0.65 BSC		
Overall Height	A	0.80	0.90	1.00	
Standoff	A1	0.00 0.02 0.05			
Contact Thickness	A3	0.20 REF			
Overall Width	E	4.00 BSC			
Exposed Pad Width	E2	2.50 2.65 2.80			
Overall Length	D	4.00 BSC			
Exposed Pad Length	D2	2.50	2.65	2.80	
Contact Width	b	0.25 0.30 0.3		0.35	
Contact Length	L	0.30 0.40 0.50		0.50	
Contact-to-Exposed Pad	К	0.20 – –			

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Package is saw singulated.

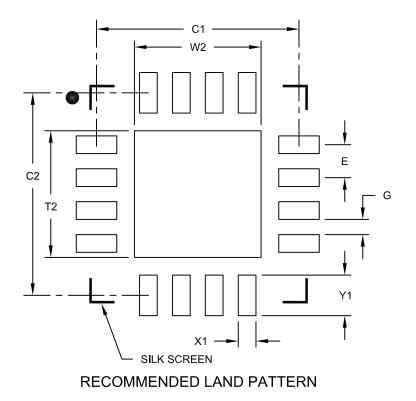
3. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-127B

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	E	0.65 BSC			
Optional Center Pad Width	W2	2.50			
Optional Center Pad Length	T2			2.50	
Contact Pad Spacing	C1	4.00			
Contact Pad Spacing	C2		4.00		
Contact Pad Width (X16)	X1			0.35	
Contact Pad Length (X16)	Y1			0.80	
Distance Between Pads	G	0.30			

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2127A

NOTES:

# APPENDIX A: REVISION HISTORY

#### **Revision D (March 2012)**

The following is the list of modifications:

Added the MSOP (8L) package for MCP662 and all related information throughout the document.

## **Revision C (November 2011)**

The following is the list of modifications:

- Added the SOT-23 (5L) and TDFN (8L) package option for MCP661 and SOT-23 (6L) package options for MCP663 and the related information throughout the document. Updated Package Types drawing with pin designation for each new package.
- 2. Updated Table 1-4 to show the temperature specifications for new packages.
- 3. Updated Table 3-1 to show all the pin functions.
- Updated Section 6.0 "Packaging Information" with markings for the new additions. Added the corresponding SOT-23 (5L and 6L) and 2x3 TDFN (8L) package options and related information.
- 5. Updated table description and examples in the **Product Identification System** section.

## **Revision B (September 2011)**

The following is the list of modifications:

- 1. Added the MCP660, MCP664 and MCP669 amplifiers to the product family and the related information throughout the document.
- Added the 4x4 QFN (16L) package option for MCP660 and MCP669, SOIC and TSSOP (14L) package options for MCP660 and MCP665 and the related information throughout the document. Updated **Package Types** drawing with pin designation for each new package.
- 3. Updated Table 1-4 to show the temperature specifications for new packages.
- 4. Updated Table 3-1 to show all the pin functions.
- Updated Section 6.0 "Packaging Information" with markings for the new additions. Added the corresponding SOIC and TSSOP (14L), and 4x4 QFN (16L) package options and related information.
- 6. Updated table description and examples in **Product Identification System**.

## Revision A (July 2009)

Original release of this document.

NOTES:

# **PRODUCT IDENTIFICATION SYSTEM**

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NOX</u>		/XX		Examples:			
Device Tem	T perature ange	Package	a)	MCP660T-E/ML:	Tape and Reel Extended temperature, 16LD QFN package		
Device:	MCP660	Triple Op Amp	b)	MCP660T-E/SN:	Tape and Reel Extended temperature, 14LD SOIC package		
Device.	MCP660T MCP661	Triple Op Amp (Tape and Reel) (SOIC, TSSOP, QFN) Single Op Amp	c)	MCP660T-E/ST:	Tape and Reel Extended temperature, 14LD TSSOP package		
	MCP661T MCP662 MCP662T	Single Op Amp (Tape and Reel) (SOIC SOT-23 and TDFN) Dual Op Amp Dual Op Amp (Tape and Reel)	d)	MCP661T-E/SN:	Tape and Reel Extended temperature, 8LD SOIC package		
	MCP663 MCP663T	(DFN, MSOP and S <u>OIC</u> ) Single Op Amp with <u>CS</u> Single Op Amp with CS (Tape and Reel) (SOIC and SOT-23)	e)	MCP661T-E/MNY:	Tape and Reel, Extended Temperature 8LD TDFN package		
	MCP664 MCP664T	Quad Op Amp Quad Op Amp (Tape and Reel) (SOIC, TSSOP)	f)	MCP662T-E/MF:	Tape and Reel Extended temperature, 8LD DFN package		
	MCP665 MCP665T MCP669	Dual Op Amp with <u>CS</u> Dual Op Amp with CS (Tape and Reel) (DFN and MSOP) Quad Op Amp with <u>CS</u>	g)	MCP662T-E/MS:	Tape and Reel Extended temperature, 8LD MSOP package		
	MCP669T	Quad Op Amp with CS (Tape and Reel) (QFN)	h)	MCP662T-E/SN:	Tape and Reel Extended temperature, 8LD SOIC package		
Temperature Range:	E = -40°	C to +125°C	i)	MCP663T-E/SN:	Tape and Reel Extended temperature, 8LD SOIC package		
Package:	MF = Plas	tic Small Outline (SOT-23), 6-lead tic Dual Flat, No Lead (3×3 DFN), ad, 10-lead	j)	MCP663T-E/CHY:	Tape and Reel, Extended Temperature, 6LD SOT-23 package		
	(4x4	tic Quad Flat, No Lead Package (4x4 QFN), x0.9 mm), 16-lead tic Dual Flat, No Lead (2x3 TDFN),	k)	MCP664T-E/SN:	Tape and Reel Extended temperature, 14LD SOIC package		
	MS = Plas OT = Plas	tic Micro Small Outline (MSOP), 8-lead tic Small Outline (SOT-23), 5-lead tic Small Outline, Narrow, (3.90 mm SOIC),	I)	MCP664T-E/ST:	Tape and Reel Extended temperature, 14LD TSSOP package		
	SN = Plas	tic Small Outline (3.90 mm), 8-lead tic Thin Shrink Small Outline, (4.4 mm TSSOP),	m)	MCP665T-E/MF:	Tape and Reel Extended temperature, 10LD DFN package		
	UN = Plas * Y = Nickel	tic Micro Small Outline (MSOP), 10-lead palladium gold manufacturing designator. le on the TDFN package.	n)	MCP665T-E/UN:	Tape and Reel Extended temperature, 10LD MSOP package		
			o)	MCP669T-E/ML:	Tape and Reel Extended temperature, 16LD QFN package		

NOTES:

#### Note the following details of the code protection feature on Microchip devices:

- · Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
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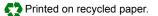
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# 08 Mar 2012

Data Sheet - MCP660/1/2/3/4/5/9 60 MHz, 6mA Op Amps Data Sheet Data Sheet Document Revision

# SYST-08YYWP715

Microchip has released a new DeviceDoc for the MCP660/1/2/3/4/5/9 60 MHz, 6mA Op Amps Data Sheet of devices. If you are using one of these devices please read the document located at MCP660/1/2/3/4/5/9 60 MHz, 6mA Op Amps Data Sheet.

Notification Status: Final

**Description of Change:** 1. Added the MSOP (8L) package for MCP662 and all related information throughout the document.

Pre Change: N/A

Post Change: N/A

Impacts to Data Sheet: None

Reason for Change: To Improve Productivity

Change Implementation Status: Complete

Date Document Changes Effective: 08 Mar 2012

**NOTE:** Please be advised that this is a change to the document only the product has not been changed..

Markings to Distinguish Revised from Unrevised Devices:N/A

# Attachments:

MCP660/1/2/3/4/5/9 60 MHz, 6mA Op Amps Data Sheet

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